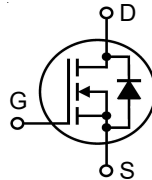


# X4-Class Power MOSFET

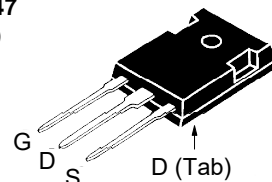
## IXTH60N20X4

$V_{DSS} = 200V$   
 $I_{D25} = 60A$   
 $R_{DS(on)} \leq 21m\Omega$

N-Channel Enhancement Mode  
Avalanche Rated



TO-247  
(IXFH)



G = Gate      D = Drain  
 S = Source    Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ C$ to $175^\circ C$	200	V
$V_{DGR}$	$T_J = 25^\circ C$ to $175^\circ C$ , $R_{GS} = 1M\Omega$	200	V
$V_{GS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ C$	60	A
$I_{DM}$	$T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$	106	A
$I_A$	$T_C = 25^\circ C$	30	A
$E_{AS}$	$T_C = 25^\circ C$	350	mJ
dv/dt	$I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ C$	50	V/ns
$P_D$	$T_C = 25^\circ C$	250	W
$T_J$		-55 ... +175	$^\circ C$
$T_{JM}$		175	$^\circ C$
$T_{stg}$		-55 ... +175	$^\circ C$
$T_L$	Maximum Lead Temperature for Soldering 1.6 mm (0.062 in.) from Case for 10s	300	$^\circ C$
$M_d$	Mounting Torque	1.13 / 10	Nm/lb.in
Weight		6	g

### Features

- International Standard Package
- Low  $R_{DS(ON)}$  and  $Q_G$
- Avalanche Rated
- Low Package Inductance

### Advantages

- High Power Density
- Easy to Mount
- Space Savings

### Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = 250\mu A$	200		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	2.5		4.5 V
$I_{GSS}$	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$			$\pm 100$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0V$ $T_J = 150^\circ C$			5 $\mu A$ 300 $\mu A$
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1	17.6	21.0	m $\Omega$

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
$g_{fs}$	$V_{DS} = 10\text{V}, I_D = 0.5 \cdot I_{D25}$ , Note 1	34	56	S
$R_{Gi}$	Gate Input Resistance		7.45	$\Omega$
$C_{iss}$	} $V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		2450	pF
$C_{oss}$			406	pF
$C_{rss}$			0.95	pF
<b>Effective Output Capacitance</b>				
$C_{o(er)}$	Energy related } $V_{GS} = 0\text{V}$		240	pF
$C_{o(tr)}$	Time related } $V_{DS} = 0.8 \cdot V_{DSS}$		880	pF
$t_{d(on)}$	} <b>Resistive Switching Times</b> $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 5\Omega$ (External)		13	ns
$t_r$			22	ns
$t_{d(off)}$			52	ns
$t_f$			10	ns
$Q_{g(on)}$	} $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		33	nC
$Q_{gs}$			9	nC
$Q_{gd}$			11	nC
$R_{thJC}$				0.60 $^\circ\text{C/W}$
$R_{thCS}$		0.21		$^\circ\text{C/W}$

**Source-Drain Diode**

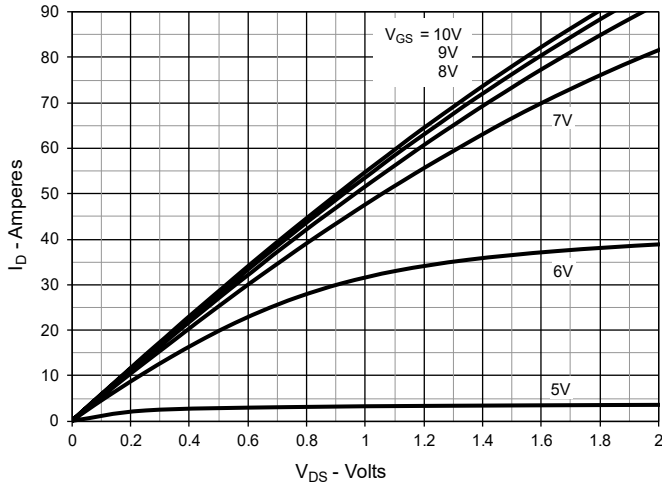
Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
$I_S$	$V_{GS} = 0\text{V}$			60 A
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			240 A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{V}$ , Note 1			1.4 V
$t_{rr}$	} $I_F = 30\text{A}, -di/dt = 200\text{A}/\mu\text{s}$ $V_R = 100\text{V}$		107	ns
$Q_{RM}$			920	nC
$I_{RM}$			17	A

 Note 1: Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ 

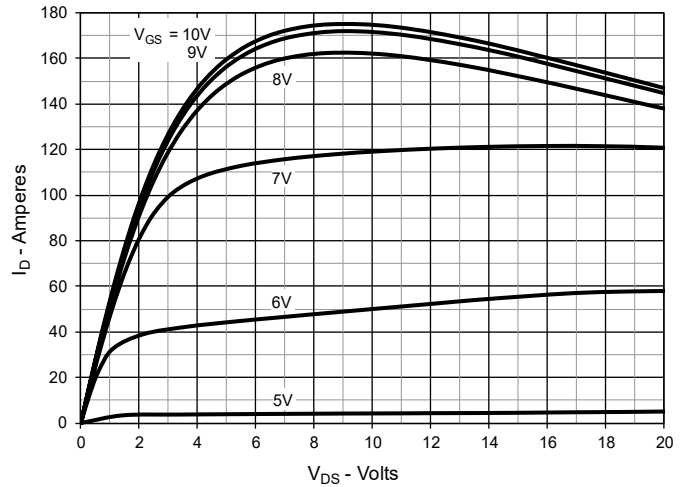
Littelfuse reserves the right to change limits, test conditions and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123B1	6,534,343	6,710,405B2	6,759,692	7,063,975B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

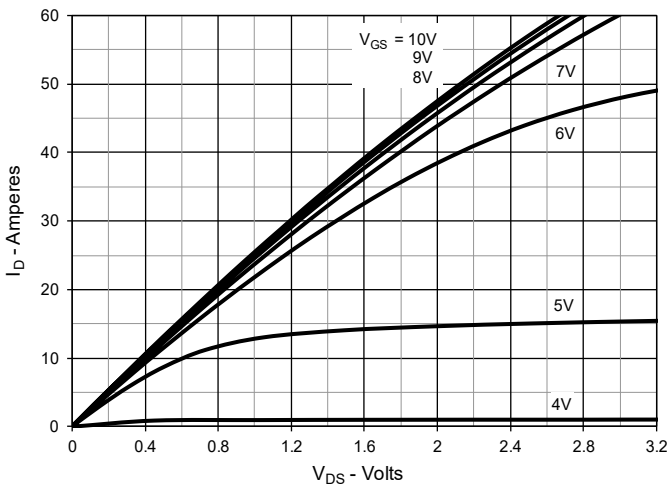
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



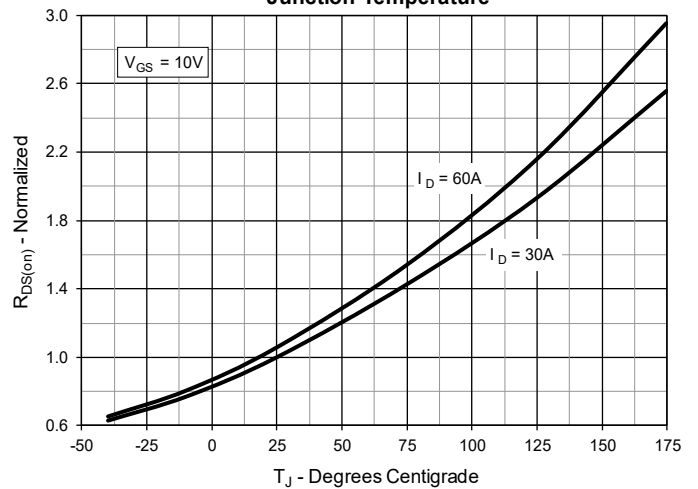
**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**



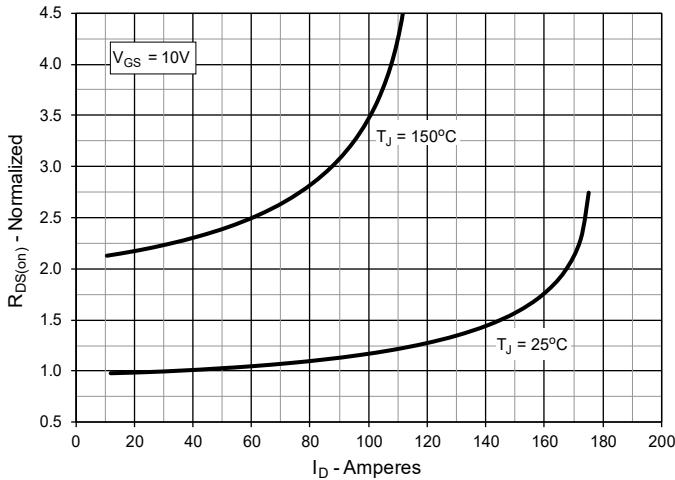
**Fig. 3. Output Characteristics @  $T_J = 150^\circ\text{C}$**



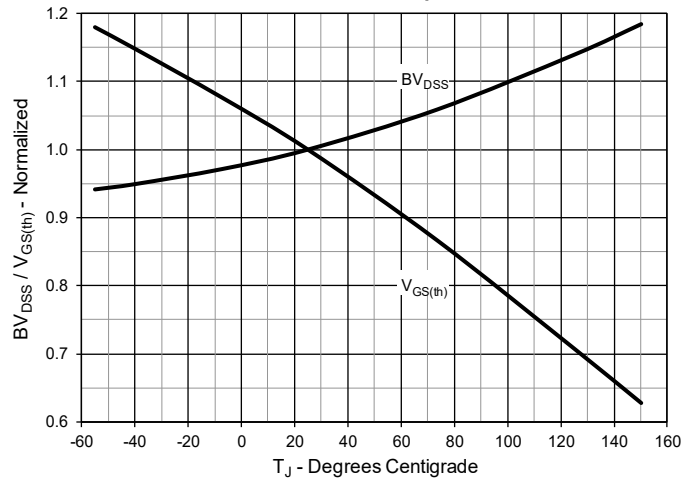
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 30\text{A}$  Value vs. Junction Temperature**



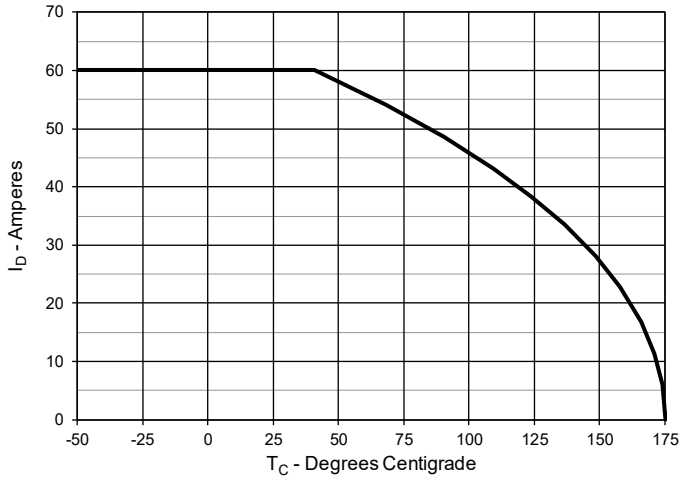
**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 30\text{A}$  Value vs. Drain Current**



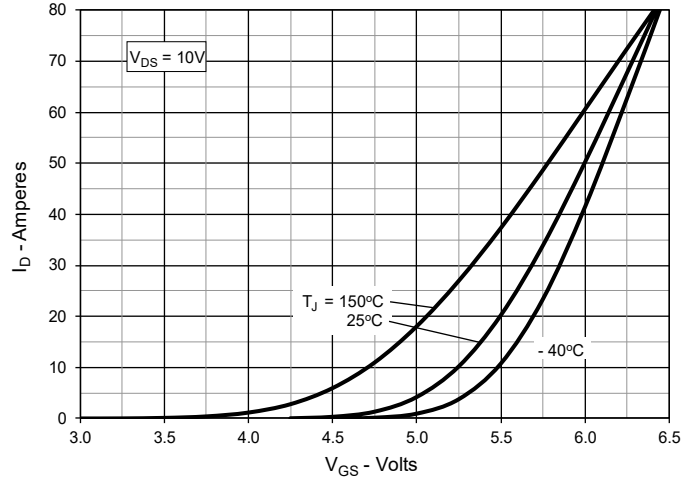
**Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature**



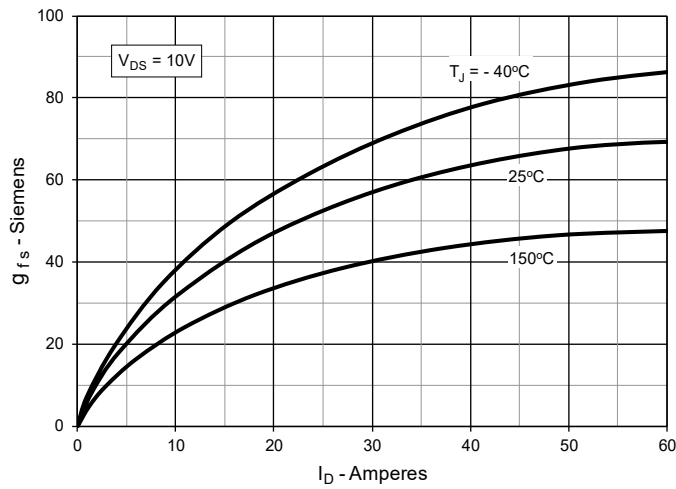
**Fig. 7. Maximum Drain Current vs. Case Temperature**



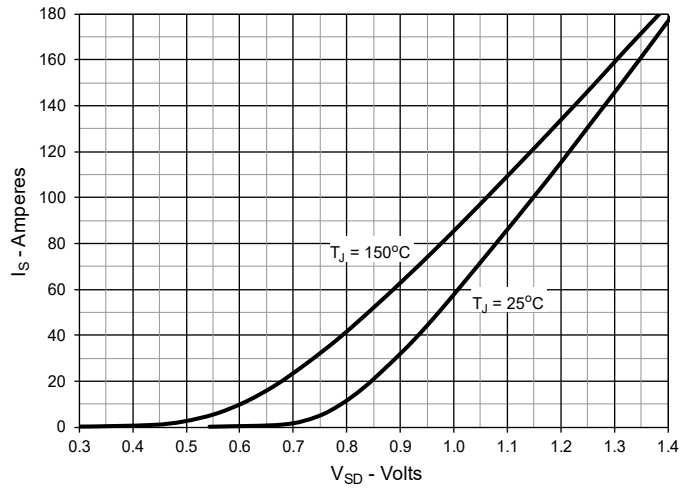
**Fig. 8. Input Admittance**



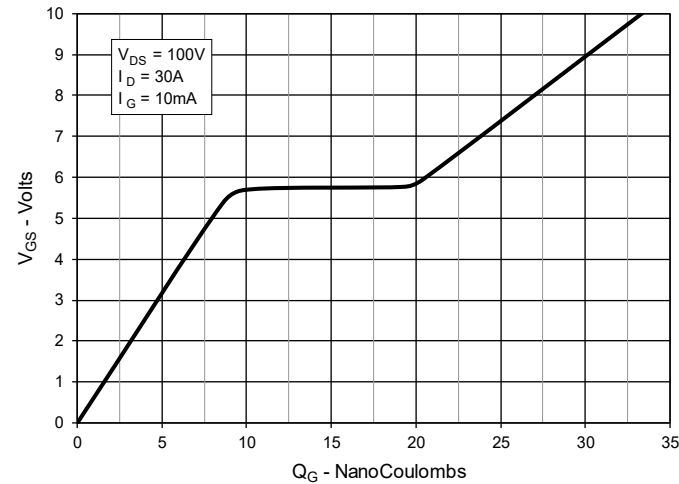
**Fig. 9. Transconductance**



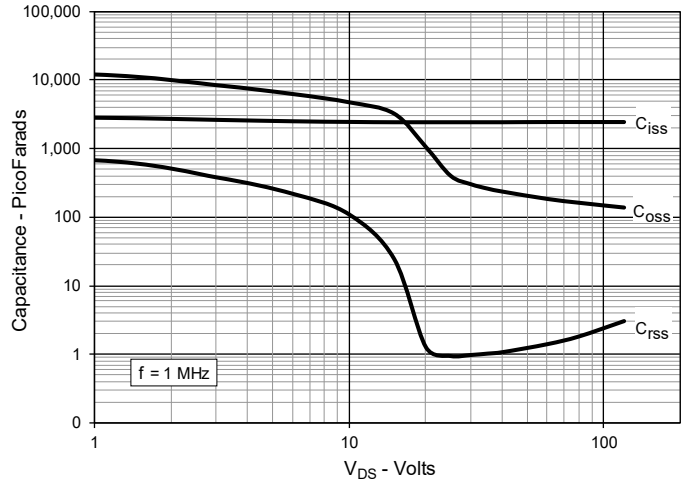
**Fig. 10. Forward Voltage Drop of Intrinsic Diode**



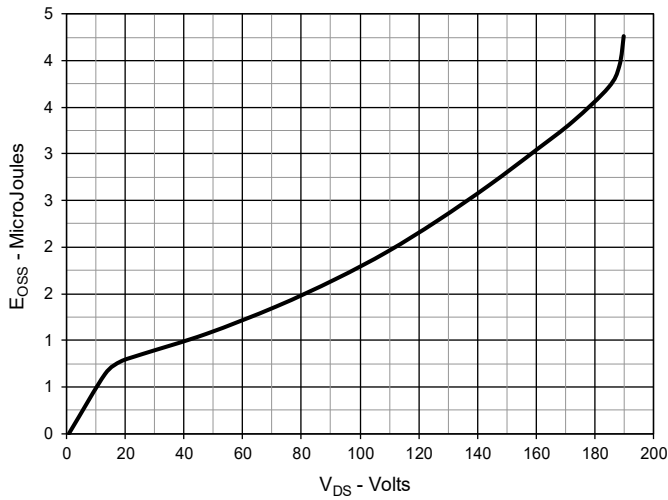
**Fig. 11. Gate Charge**



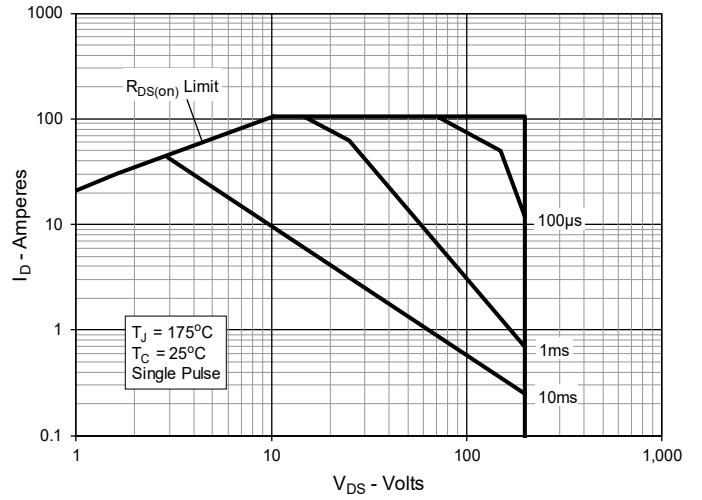
**Fig. 12. Capacitance**



**Fig. 13. Output Capacitance Stored Energy**



**Fig. 14. Forward-Bias Safe Operating Area**



**Fig. 15. Maximum Transient Thermal Impedance**

